ADE-208-093A(Z)3

HSM2692
Silicon Epitaxial Planar Diode for Tuner Band Switch

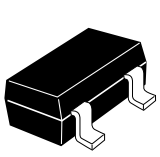
HITACHI

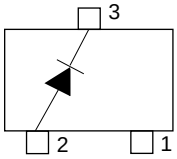
Preliminary
Rev. 1
Jun. 1993

Features

- Low forward resistance. (r_f =0.9Ω max)
- Low capacitance. (C =1.2pF max)
- MPAK package is suitable for high density surface mounting and high speed assembly.

Pin Arrangement





(Top View)

1 NC
2 Anode
3 Cathode

Ordering Information

Type No.	Laser Mark	Package Code
HSM2692	B 1	MPAK

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Value	Unit
Reverse voltage	V_R	35	V
Power dissipation	p_d	150	mW
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	-45 to +125	°C
Operation temperature	T_{opr}	-20 to +60	°C

Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse voltage	V_R	35	—	—	V	I_R = 10 µA
Reverse current	I_R	—	—	50	nA	V_R = 25 V
Forward voltage	V_F	—	—	1.0	V	I_F = 10 mA
Capacitance	C	—	—	1.2	pF	V_R= 6 V, f = 1 MHz
Forward resistance	r_f	—	—	0.9	Ω	I_F= 2mA, f=100 MHz

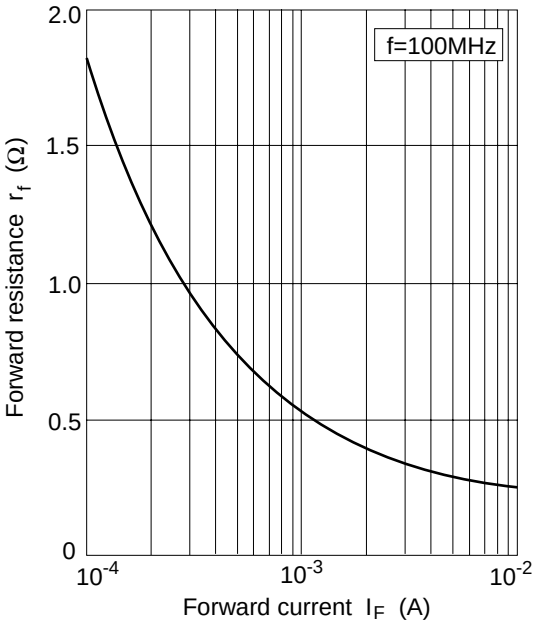


Fig.1 Forward resistance Vs. Forward current

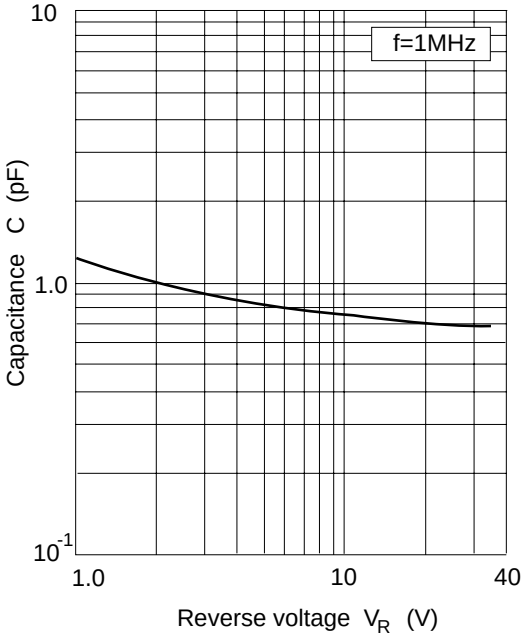


Fig.2 Capacitance Vs. Reverse voltage

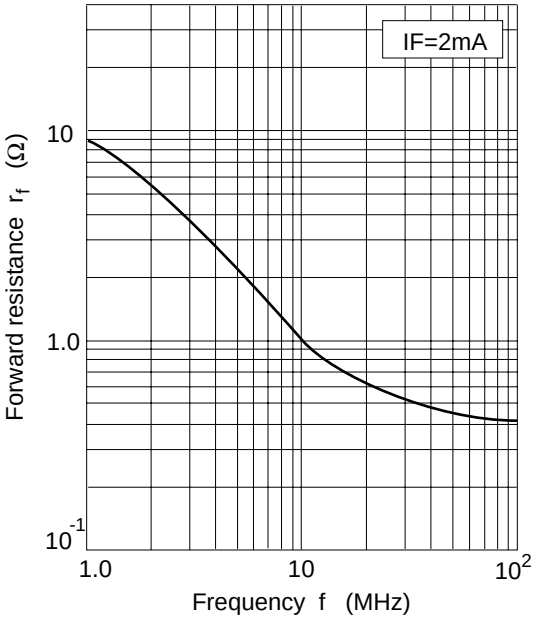
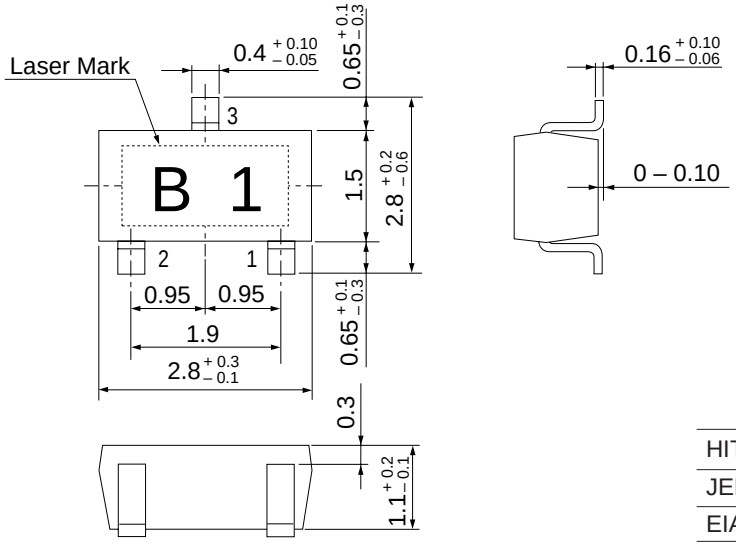


Fig.3 Forward resistance Vs. Frequency

Package Dimensions

Unit: mm



1 NC
2 Anode
3 Cathode

HITACHI Code	MPAK(1)
JEDEC Code	—
EIAJ Code	SC-59A
Weight (g)	0.011